

31980 U.S. PTO  
10032563  
01/02/2002

PATENT NUMBER and  
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10032563	01/02/2002	438	504	282	3

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\*\*CONTINUING DATA VERIFIED:

\*\* FOREIGN APPLICATIONS VERIFIED:

JAPAN 2001-019549 01/29/2001

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	ATTORNEY DOCKET NO
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no			740819-723
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no			
Verified and Acknowledged Examiners's initials			
TITLE : Method of manufacturing nitride semiconductor substrate			

U.S. DEPT. OF COMM./PAT & TM-PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
Assistant Examiner		DRAWING	
Amount Due		Sheets Drwg.	Figs. Drwg.
Date Paid		Print Fig.	
Primary Examiner		Application Examiner	
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